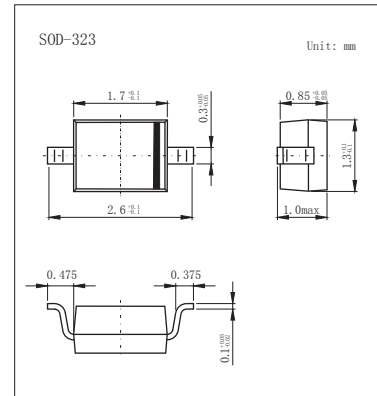


## Schottky Diodes

## BAT60B (KAT60B)

## ■ Features

- High Current Rectifier Schottky Diode with Low  $V_f$  Drop
- Low Voltage, Low Inductance
- For Power Supply
- For Detection and Step-up-Conversion

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
DC Blocking Voltage	$V_R$	10	V
Forward Current	$I_F$	3	A
Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	$I_{FSM}$	5	
Power Dissipation	$P_D$	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	286	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_R$	$I_R = 1\text{ mA}$	10			V
Forward voltage	$V_{F1}$	$I_F = 100\text{ mA}$			0.38	
	$V_{F2}$	$I_F = 500\text{ mA}$			0.5	
	$V_{F3}$	$I_F = 1000\text{ mA}$			0.6	
Reverse voltage leakage current	$I_{R1}$	$V_R = 5\text{ V}$			15	$\mu\text{A}$
	$I_{R2}$	$V_R = 8\text{ V}$			25	
Capacitance between terminals	$C_T$	$V_R = 5\text{ V}, f = 1\text{ MHz}$		30		pF

## ■ Marking

Marking	W5 •
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# Schottky Diodes

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■ Typical Characteristics

